CLAIMS

1. A sputtering target material consisting of an alloy,

wherein the alloy consists of Ta and Cr with the balance being unavoidable impurities, and

wherein the sputtering target material has a bending strength of 400 MPa or more as measured by a three-point bending test.

2. The sputtering target material according to claim 1, wherein the sputtering target material has a relative density of 97% or more as measured by the Archimedes' method.

3. The sputtering target material according to claim 1 or 2, wherein the sputtering target material has a Cr phase, a Ta phase, and a Cr_2Ta phase.

4. The sputtering target material according to claim 3, wherein the ratio (Px) of the intensity of Cr_2Ta (220) to the intensity of Ta (110) in the X-ray diffraction (XRD) pattern is 10% or less.

5. The sputtering target material according to claim 3 or 4, wherein the Cr_2Ta phase is present on a surface of the Cr phase, and wherein the thickness (Tave) of the Cr_2Ta phase is 30 μm or less.